



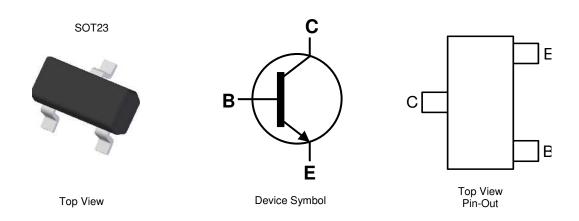
40V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type: MMBT4403
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under separate datasheet (MMBT4401Q)

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic "Green" Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.008 grams (Approximate)



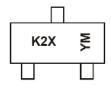
Ordering Information (Note 4)

Ī	Part Number	Package	Marking Reel Size (inches)		Tape Width (mm)	Packing	
	Part Number	rackage	wa King	neer Size (Inches)	rape widin (ililii)	Qty.	Carrier
	MMBT4401-7-F	SOT23	K2X	7	8	3,000	Reel
	MMBT4401-13-F	SOT23	K2X	13	8	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K2X = Product Type Marking Code YM = Date Code Marking $Y \text{ or } \overline{Y} = Year (ex: K = 2023)$ $M \text{ or } \overline{M} = Month (ex: 9 = September)$

Date Code Key

Year	2010	-	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	Х	-	K	L	М	N	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@ TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	VCEO	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	lc	600	mA
Peak Collector Current	Ісм	1	Α
Peak Base Current	Івм	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Dower Discipation	(Note 5)	D-	310	mW
Power Dissipation	(Note 6)	PD	350	IIIVV
Thermal Resistance, Junction to Ambient	(Note 5)	Б	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	357	- °C/VV
Thermal Resistance, Junction to Leads	(Note 7)	ReJL	350	°C/W
Thermal Resistance, Junction to Case	Rejc	120	°C/W	
Operating and Storage Temperature Range		TJ,TSTG	-55 to +150	°C

ESD Ratings (Note 8)

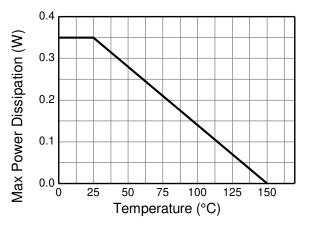
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С
Electrostatic Discharge – Charged Device Model	ESD CDM	1,000	V	C3

Notes:

^{5.} For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air For a device mounted of minimum recommended pad layout 102 copper that is a conditions whilst operating in a steady-state.
 Same as note (5), except the device is mounted on 15mm x 15mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the leads).
 Refer to JEDEC specification JESD22-A114, JESD22-A115 and JES-022-C101.



Thermal Characteristics and Derating Information



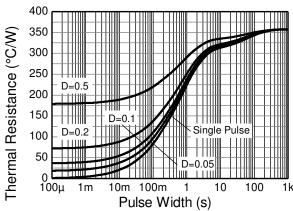
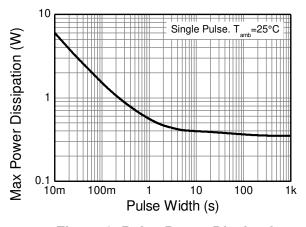


Figure 1. Derating Curve

Figure 2. Transient Thermal Impedance



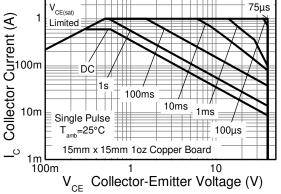


Figure 3. Pulse Power Dissipation

Figure 4. Safe Operating Area

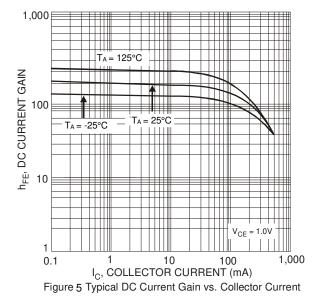


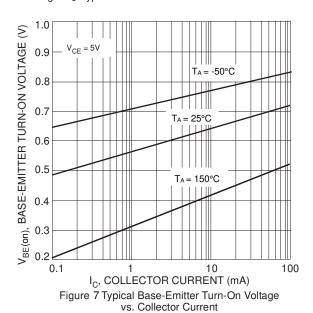
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	ВУсво	60	_	V	Ic = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BVCEO	40	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	V	I _E = 100μA
Collector Cutoff Current	I _{CEX}	_	100	nA	$V_{CE} = 35V, V_{EB(off)} = 0.4V$
Base Cutoff Current	I _{BL}	_	100	nA	$V_{CE} = 35V, V_{EB(off)} = 0.4V$
ON CHARACTERISTICS (Note 9)					
DC Current Gain	hFE	20 40 80 100 40		_	$\begin{split} &I_{C} = \ 100 \mu A, \ V_{CE} = 1V \\ &I_{C} = \ 1mA, \ V_{CE} = 1V \\ &I_{C} = \ 10mA, \ V_{CE} = 1V \\ &I_{C} = \ 150mA, \ V_{CE} = 1V \\ &I_{C} = \ 500mA, \ V_{CE} = 2V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.4 0.75	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.75 —	0.95 1.2	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	Ccb	_	6.5	pF	VcB = 5V, f = 1MHz
Input Capacitance	Ceb	_	30	pF	$V_{EB} = 0.5V, f = 1MHz$
Input Impedance	h _{ie}	1	15	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	8	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1mA,$
Small Signal Current Gain	h _{fe}	40	500	_	f = 1kHz
Output Admittance	hoe	1	30	μS	
Current Gain-Bandwidth Product	f _T	250	_	MHz	V _{CE} = 10V, I _C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	td	_	15	ns	Vcc = 30V, Ic = 150mA,
Rise Time	t _r	_	20	ns	$V_{BE(off)} = 2V, I_{B1} = 15mA$
Storage Time	ts	_	225	ns	Vcc = 30V, Ic = 150mA,
Fall Time	t _f		30	ns	$I_{B1} = -I_{B2} = 15mA$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.







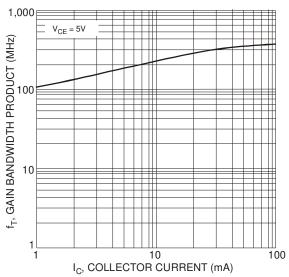


Figure 9 Typical Gain Bandwidth Product vs. Collector Current

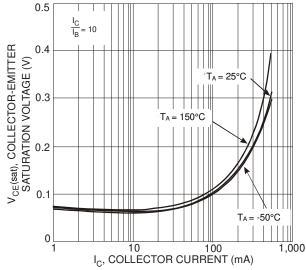


Figure 6 Collector-Emitter Saturation Voltage vs. Collector Current

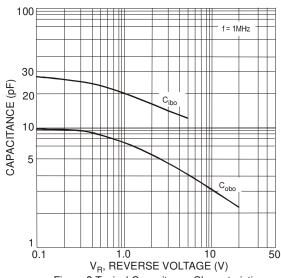


Figure 8 Typical Capacitance Characteristics

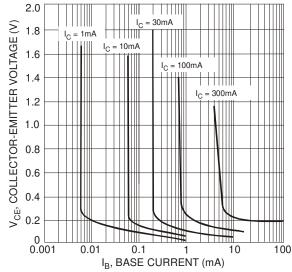


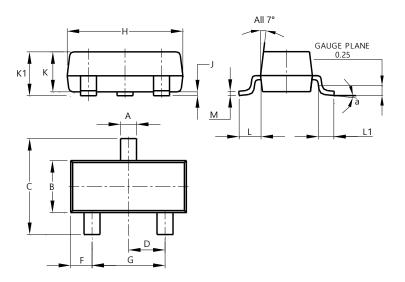
Figure 10 Typical Collector Saturation Region



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

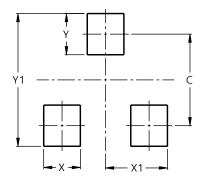


	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

 $\label{lem:please} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
V1	2.0



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